



# HJ122

NPN EPITAXIAL PLANAR TRANSISTOR

## Description

The HJ122 is designed for use in general purposes and low speed switching applications.

## Features

- High DC current gain
- Built-in a damper diode at E-C

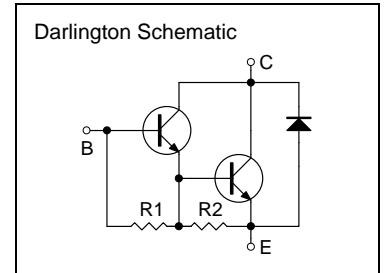
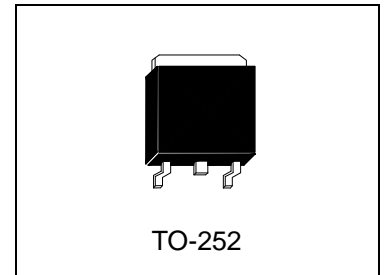
## Absolute Maximum Ratings (T<sub>A</sub>=25°C)

- Maximum Temperatures
  - Storage Temperature ..... -55 ~ +150 °C
  - Junction Temperature ..... +150 °C
- Maximum Power Dissipation
  - Total Power Dissipation (T<sub>C</sub>=25°C) ..... 20 W
- Maximum Voltages and Currents (T<sub>A</sub>=25°C)
  - BV<sub>CBO</sub> Collector to Base Voltage ..... 100 V
  - BV<sub>CEO</sub> Collector to Emitter Voltage ..... 100 V
  - BV<sub>EBO</sub> Emitter to Base Voltage ..... 5 V
  - I<sub>C</sub> Collector Current ..... 5 A

## Electrical Characteristics (T<sub>A</sub>=25°C)

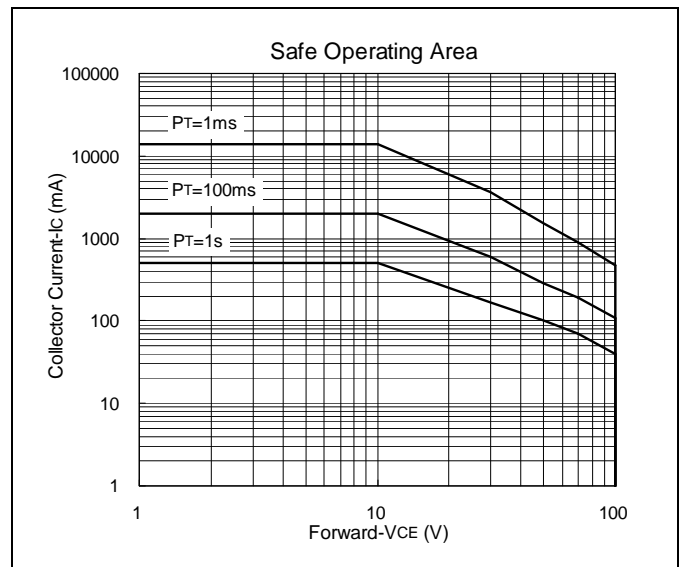
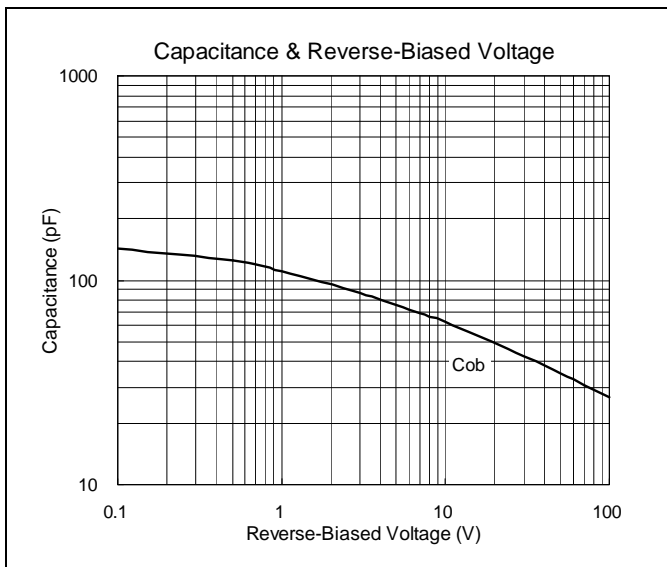
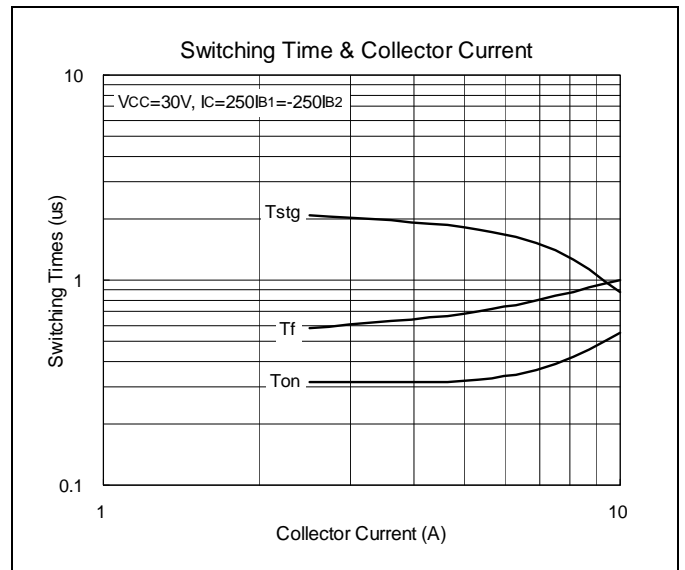
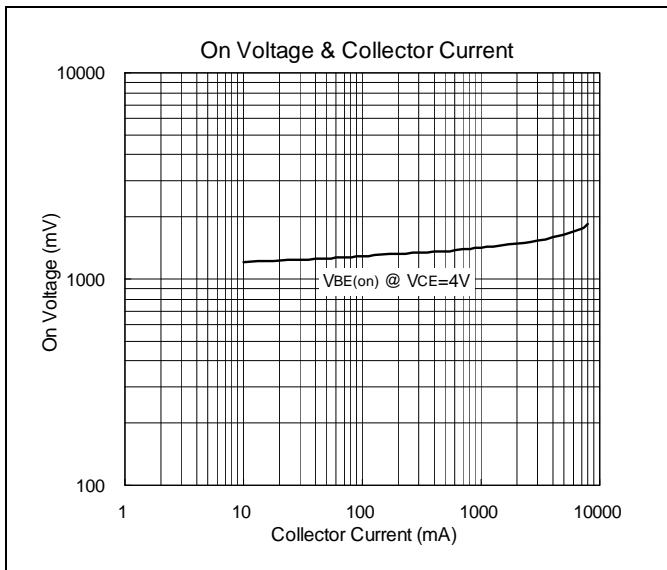
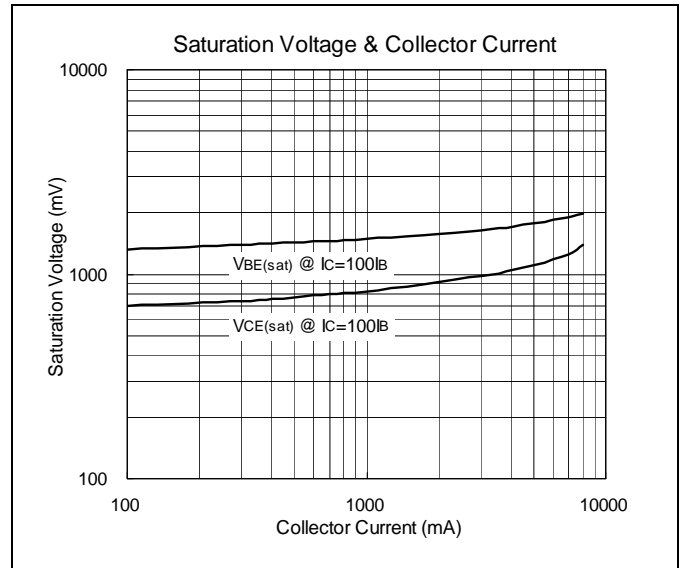
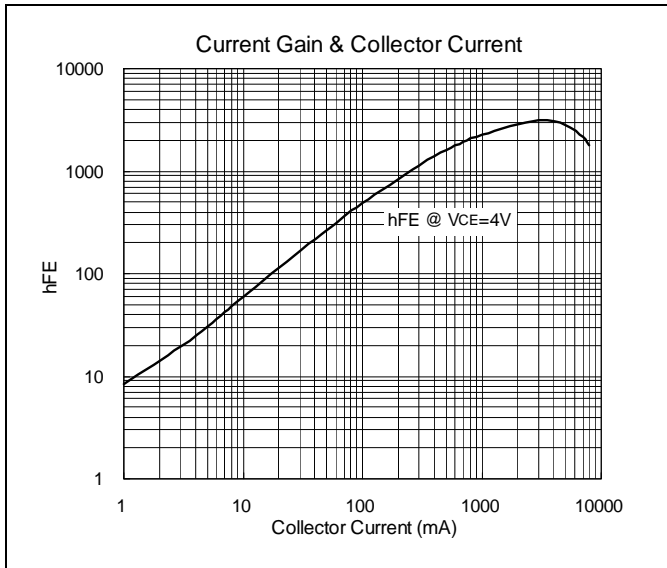
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV <sub>CBO</sub>	100	-	-	V	I <sub>C</sub> =1mA
BV <sub>EBO</sub>	5	-	-	V	I <sub>E</sub> =1mA
I <sub>CBO</sub>	-	-	10	uA	V <sub>CB</sub> =100V
I <sub>CEO</sub>	-	-	10	uA	V <sub>CE</sub> =100V
I <sub>EBO</sub>	-	-	2	mA	V <sub>EB</sub> =5V
*V <sub>CE(sat)1</sub>	-	-	2	V	I <sub>C</sub> =4A, I <sub>B</sub> =16mA
*V <sub>CE(sat)2</sub>	-	-	4	V	I <sub>C</sub> =8A, I <sub>B</sub> =80mA
*V <sub>BE(sat)</sub>	-	-	4.5	V	I <sub>C</sub> =8A, I <sub>B</sub> =80mA
*V <sub>BE(on)</sub>	-	-	2.8	V	V <sub>CE</sub> =4V, I <sub>C</sub> =4A
*h <sub>FE1</sub>	1	-	12	K	V <sub>CE</sub> =4V, I <sub>C</sub> =4A
*h <sub>FE2</sub>	100	-	-		V <sub>CE</sub> =4V, I <sub>C</sub> =8A
Cob	-	-	200	pF	V <sub>CB</sub> =10V

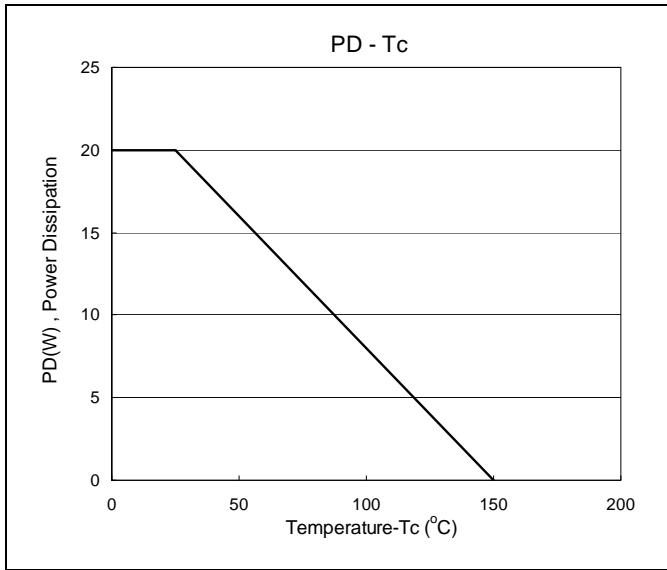
\*Pulse Test: Pulse Width ≤380us, Duty Cycle≤2%





### Characteristics Curve







### TO-252 Dimension

3-Lead TO-252 Plastic Surface Mount Package  
HSMC Package Code: J

**Marking:**

Pb Free Mark  
 Pb-Free: "●" (Note)  
 Normal: None

Note: Green label is used for pb-free packing  
 Pin Style: 1.Base 2.Collector 3.Emitter

**Material:**

- Lead solder plating: Sn60/Pb40 (Normal), Sn/3.0Ag/0.5Cu or Pure-Tin (Pb-free)
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0

DIM	Min.	Max.
A	6.35	6.80
C	4.80	5.50
F	1.30	1.70
G	5.40	6.25
H	2.20	3.00
L	0.40	0.90
M	2.20	2.40
N	0.90	1.50
a1	0.40	0.65
a2	-	*2.30
a5	0.65	1.05

\*: Typical, Unit: mm

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- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0

DIM	Min.	Max.
A	6.40	6.80
B	-	6.00
C	5.04	5.64
D	-	*4.34
E	0.40	0.80
F	0.50	0.90
G	5.90	6.30
H	2.50	3.20
I	9.20	9.80
J	0.60	1.00
K	-	0.96
L	0.66	0.86
M	2.20	2.40
N	0.70	1.10
O	0.82	1.22
a1	0.40	0.60
a2	2.10	2.50
y1	-	5°
y2	-	3°

\*: Typical, Unit: mm

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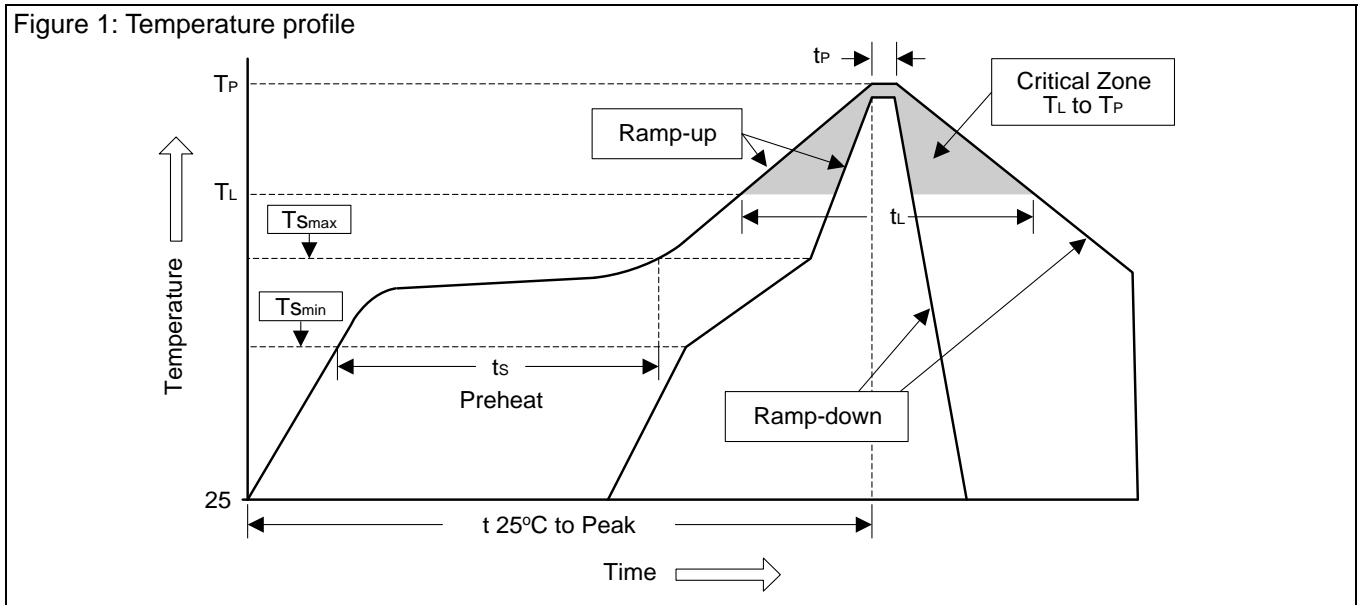
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### Soldering Methods for HSMC's Products

1. Storage environment: Temperature=10°C~35°C Humidity=65%±15%
2. Reflow soldering of surface-mount devices

Figure 1: Temperature profile



Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average ramp-up rate ( $T_L$ to $T_P$ )	<3°C/sec	<3°C/sec
Preheat		
- Temperature Min ( $T_{smin}$ )	100°C	150°C
- Temperature Max ( $T_{smax}$ )	150°C	200°C
- Time (min to max) ( $t_s$ )	60~120 sec	60~180 sec
$T_{smax}$ to $T_L$		
- Ramp-up Rate	<3°C/sec	<3°C/sec
Time maintained above:		
- Temperature ( $T_L$ )	183°C	217°C
- Time ( $t_L$ )	60~150 sec	60~150 sec
Peak Temperature ( $T_P$ )	240°C +0/-5°C	260°C +0/-5°C
Time within 5°C of actual Peak Temperature ( $t_P$ )	10~30 sec	20~40 sec
Ramp-down Rate	<6°C/sec	<6°C/sec
Time 25°C to Peak Temperature	<6 minutes	<8 minutes

### 3. Flow (wave) soldering (solder dipping)

Products	Peak temperature	Dipping time
Pb devices.	245°C ±5°C	10sec ±1sec
Pb-Free devices.	260°C ±5°C	10sec ±1sec